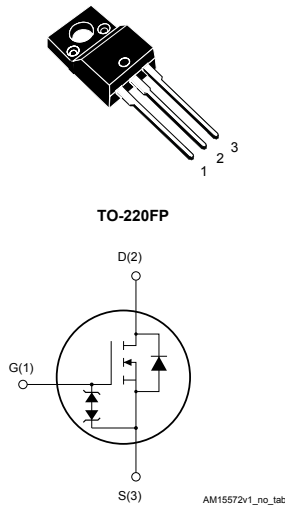


N-channel 600 V, 165 mΩ typ., 18 A, MDmesh DM6 Power MOSFET in a TO-220FP package



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STF26N60DM6	600 V	195 mΩ	18 A

- Fast-recovery body diode
- Lower $R_{DS(on)}$ per area vs previous generation
- Low gate charge, input capacitance and resistance
- 100% avalanche tested
- Extremely high dv/dt ruggedness
- Zener-protected

Applications

- Switching applications

Description

This high-voltage N-channel Power MOSFET is part of the MDmesh DM6 fast-recovery diode series. Compared with the previous MDmesh fast generation, DM6 combines very low recovery charge (Q_{rr}), recovery time (t_{rr}) and excellent improvement in $R_{DS(on)}$ per area with one of the most effective switching behaviors available in the market for the most demanding high-efficiency bridge topologies and ZVS phase-shift converters.



Product status link

[STF26N60DM6](#)

Product summary

Order code	STF26N60DM6
Marking	26N60DM6
Package	TO-220FP
Packing	Tube

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	18	A
	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	11	A
$I_{DM}^{(1)}$	Drain current (pulsed)	60	A
P_{TOT}	Total power dissipation at $T_C = 25\text{ }^\circ\text{C}$	30	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	100	V/ns
$di/dt^{(2)}$	Peak diode recovery current slope	1000	A/ μ s
$dv/dt^{(3)}$	MOSFET dv/dt ruggedness	100	V/ns
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink ($t = 1\text{ s}$, $T_C = 25\text{ }^\circ\text{C}$)	2.5	kV
T_{stg}	Storage temperature range	-55 to 150	$^\circ\text{C}$
T_J	Operating junction temperature range		

1. Pulse width is limited by safe operating area.
2. $I_{SD} \leq 18\text{ A}$, $V_{DS} (\text{peak}) < V_{(BR)DSS}$, $V_{DD} = 400\text{ V}$.
3. $V_{DS} \leq 480\text{ V}$

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	4.17	$^\circ\text{C/W}$
$R_{thj-amb}^{(1)}$	Thermal resistance junction-ambient	50	$^\circ\text{C/W}$

1. When mounted on FR-4 board of $inch^2$, 2oz Cu.

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_{Jmax})	4	A
E_{AS}	Single pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	360	mJ

2 Electrical characteristics

$T_C = 25\text{ °C}$ unless otherwise specified

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	600			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}, V_{DS} = 600\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}, V_{DS} = 600\text{ V},$ $T_C = 125\text{ °C}^{(1)}$			100	μA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}, V_{GS} = \pm 25\text{ V}$			± 5	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3.25	4	4.75	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 9\text{ A}$		165	195	$\text{m}\Omega$

1. Defined by design, not subject to production test.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}, f = 1\text{ MHz},$ $V_{GS} = 0\text{ V}$	-	940	-	pF
C_{oss}	Output capacitance		-	75	-	pF
C_{riss}	Reverse transfer capacitance		-	4	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{DS} = 0\text{ to }480\text{ V}, V_{GS} = 0\text{ V}$	-	157	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}, I_D = 0\text{ A}$	-	4.8	-	Ω
Q_g	Total gate charge	$V_{DD} = 480\text{ V}, I_D = 18\text{ A},$ $V_{GS} = 0\text{ to }10\text{ V}$ (see Figure 14. Test circuit for gate charge behavior)	-	24	-	nC
Q_{gs}	Gate-source charge		-	6	-	nC
Q_{gd}	Gate-drain charge		-	11.5	-	nC

1. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}, I_D = 9\text{ A},$ $R_G = 4.7\text{ }\Omega, V_{GS} = 10\text{ V}$	-	13	-	ns
t_r	Rise time		-	11	-	ns
$t_{d(off)}$	Turn-off delay time	(see Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform)	-	39	-	ns
t_f	Fall time		-	8	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		18	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		60	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0\text{ V}$, $I_{SD} = 18\text{ A}$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 18\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$	-	100		ns
Q_{rr}	Reverse recovery charge		-	0.35		μC
I_{RRM}	Reverse recovery current	(see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	7		A
t_{rr}	Reverse recovery time	$I_{SD} = 18\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$	-	170		ns
Q_{rr}	Reverse recovery charge		-	1.02		μC
I_{RRM}	Reverse recovery current		(see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	12	

1. Pulse width is limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5 %.

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

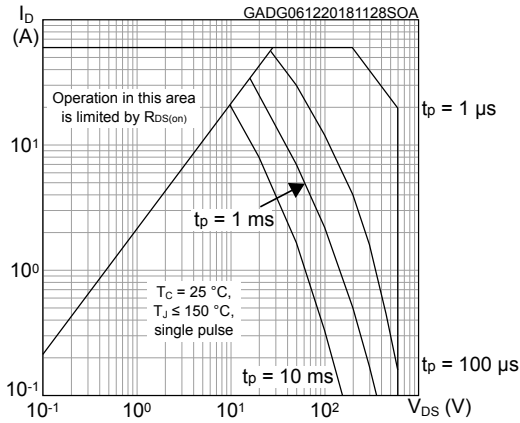


Figure 2. Normalized thermal impedance

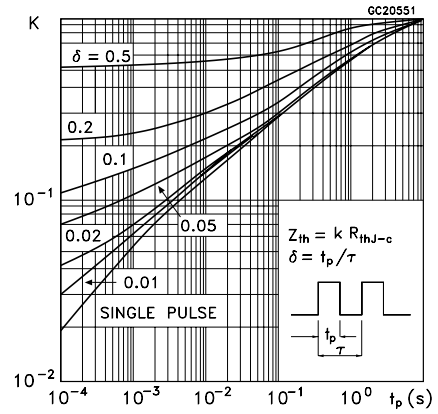


Figure 3. Output characteristics

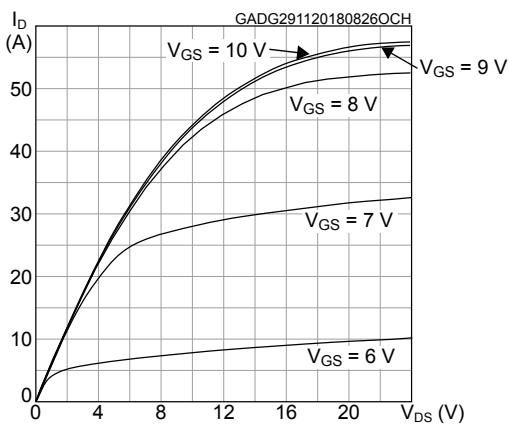


Figure 4. Transfer characteristics

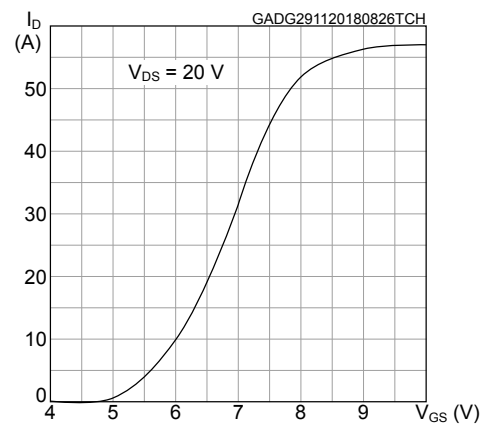


Figure 5. Gate charge vs gate-source voltage

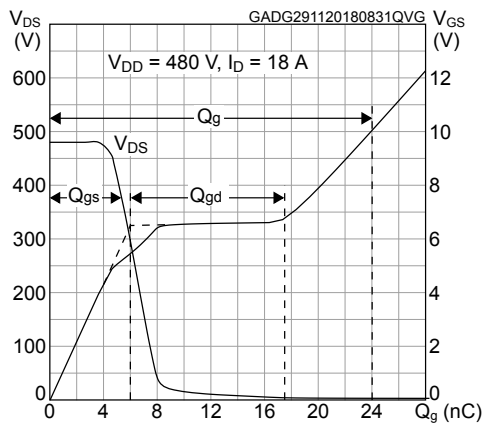


Figure 6. Capacitance variations

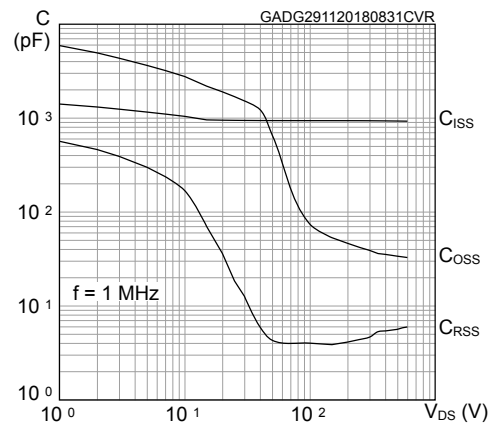


Figure 7. Static drain-source on-resistance

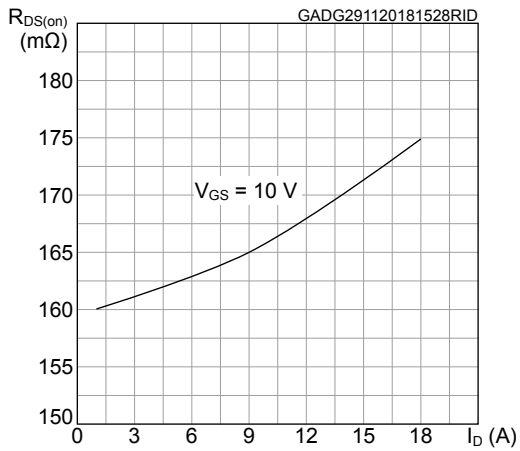


Figure 8. Normalized on-resistance vs temperature

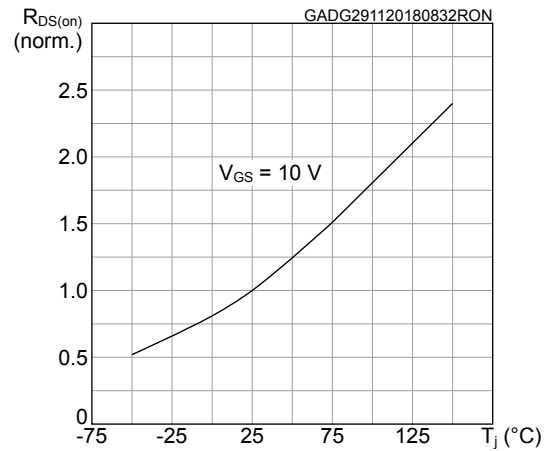


Figure 9. Normalized gate threshold voltage vs temperature

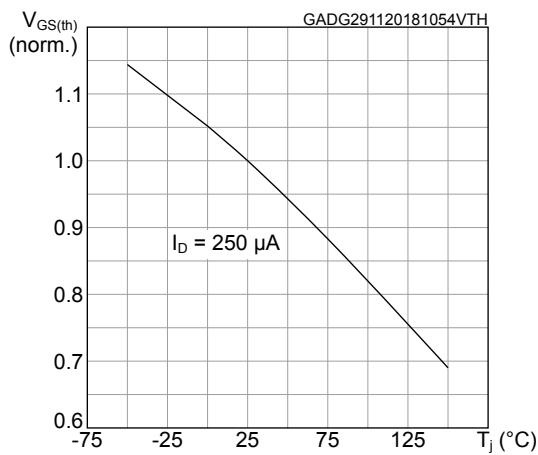


Figure 10. Normalized $V_{(BR)DSS}$ vs temperature

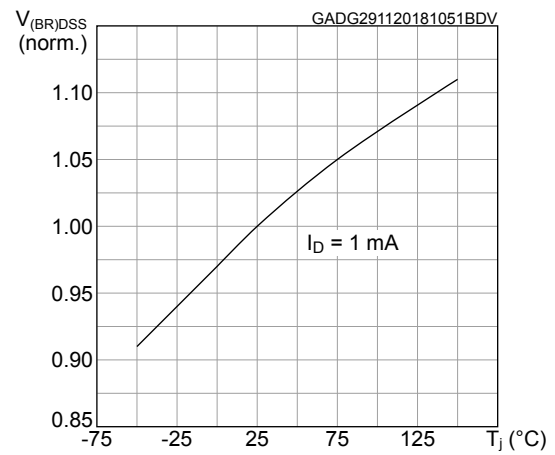


Figure 11. Output capacitance stored energy

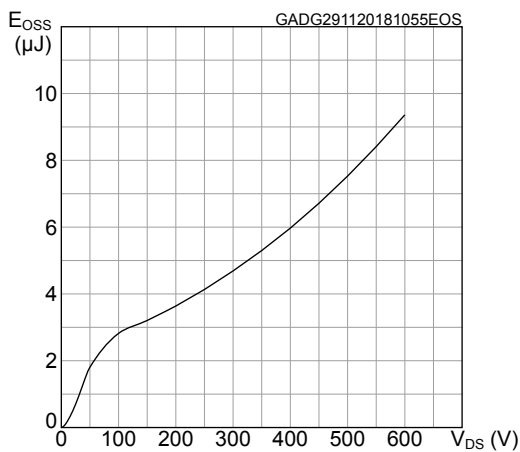
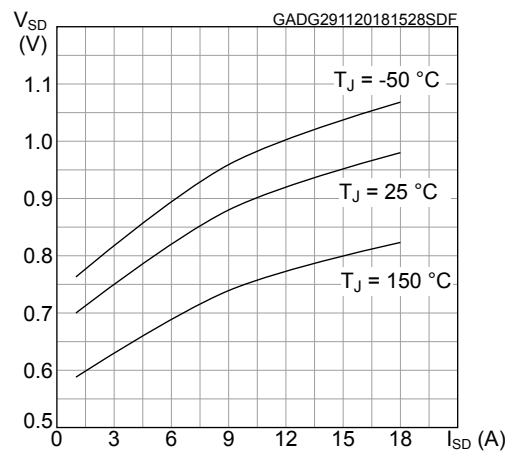
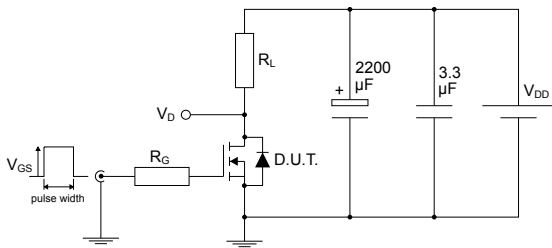


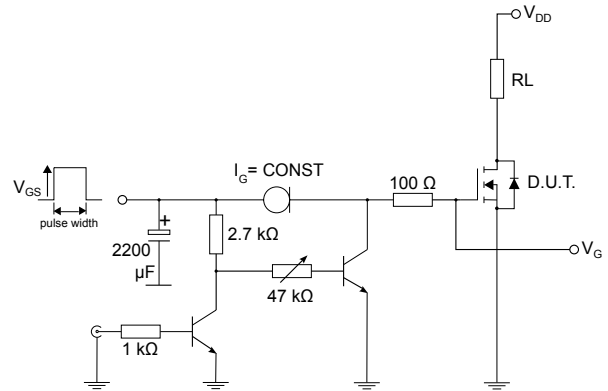
Figure 12. Source-drain diode forward characteristics



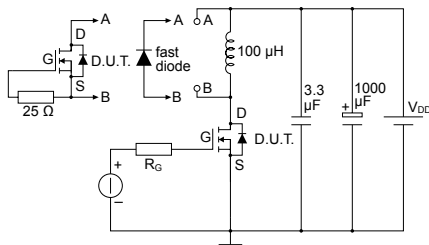
3 Test circuits

Figure 13. Test circuit for resistive load switching times


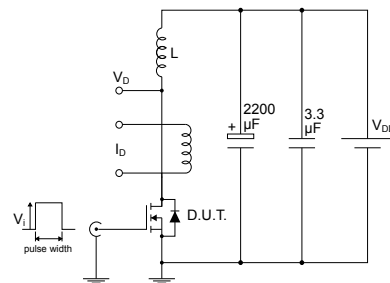
AM01468v1

Figure 14. Test circuit for gate charge behavior


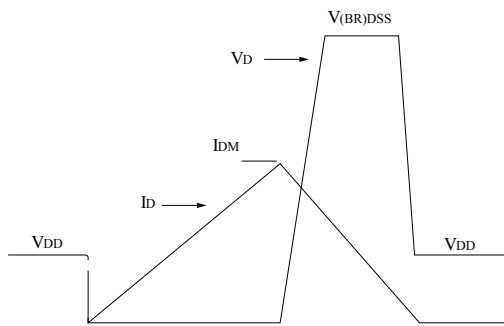
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Figure 15. Test circuit for inductive load switching and diode recovery times


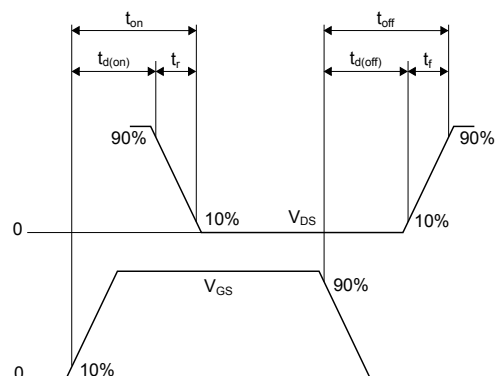
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Figure 16. Unclamped inductive load test circuit


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Figure 17. Unclamped inductive waveform


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Figure 18. Switching time waveform


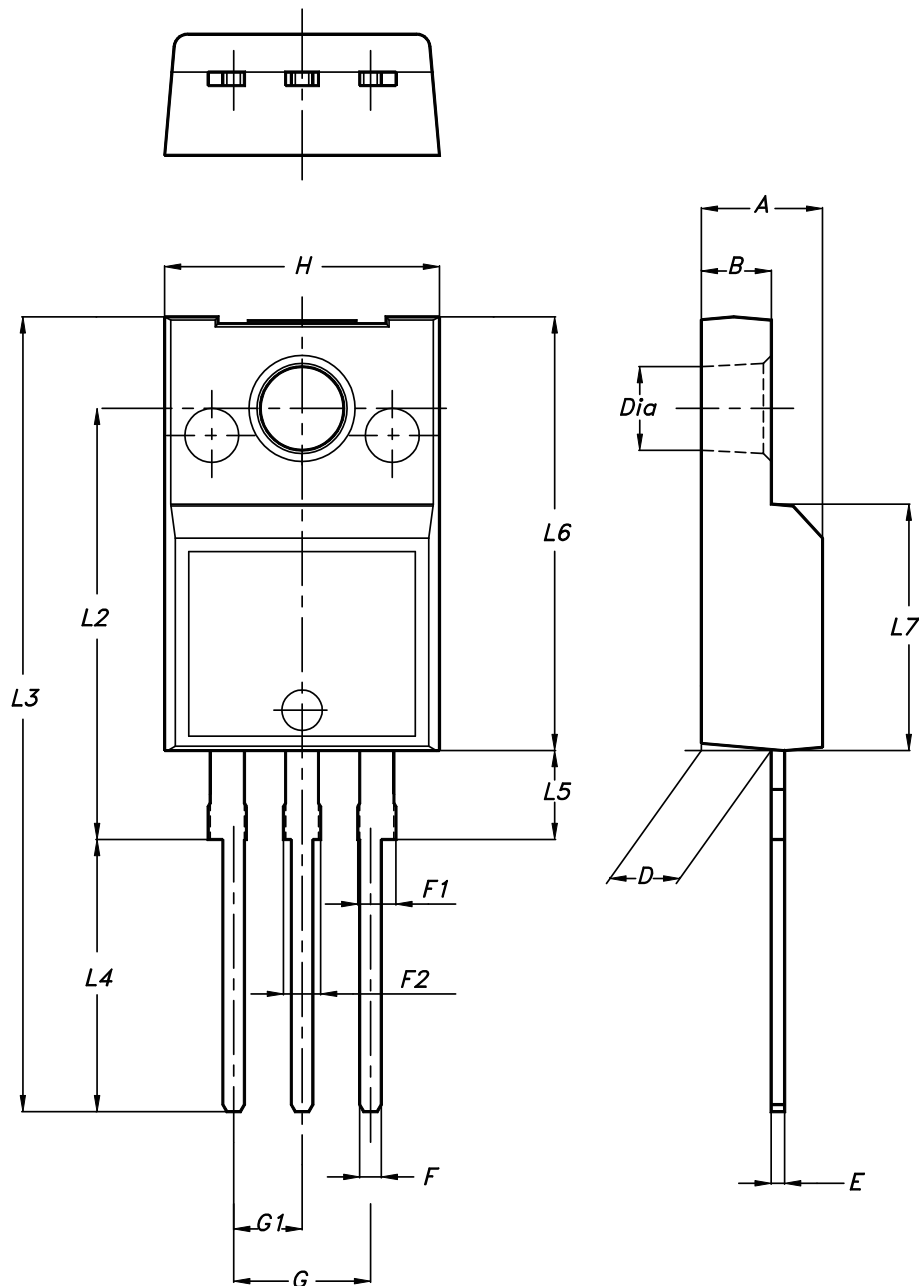
AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO-220FP package information

Figure 19. TO-220FP package outline



7012510_Rev_13_B

Table 8. TO-220FP package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
B	2.50		2.70
D	2.50		2.75
E	0.45		0.70
F	0.75		1.00
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.20
G1	2.40		2.70
H	10.00		10.40
L2		16.00	
L3	28.60		30.60
L4	9.80		10.60
L5	2.90		3.60
L6	15.90		16.40
L7	9.00		9.30
Dia	3.00		3.20

Revision history

Table 9. Document revision history

Date	Version	Changes
07-Dec-2018	1	First release.
10-Sep-2020	2	Updated Table 1 .

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